JJMICROELECTRONICS

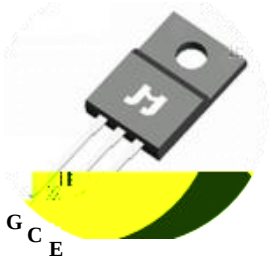
650V 10A Trench and Field Stop IGBT

JJT10N65SS

Key performance:

- $_{CE}$=650V
- $_{C}$=10A@ $_{C}$=100
- $_{CE(sat)}$=1.8 V

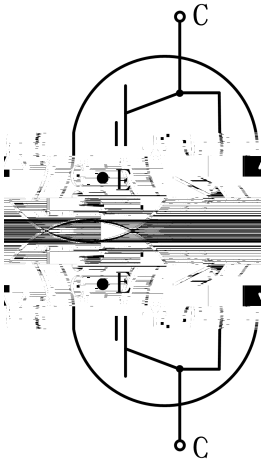
TO-220F



Features:

- High ruggedness performance
- 10μs short circuit capability
- Positive $_{CE\ (sat)}$ temperature coefficient
- High efficiency for mo nt A

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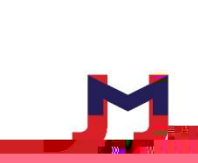
[redacted]

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$_{CES}$	Collector-emitter breakdown voltage	$_{GE}$=0V, $_{C}$=250μA	650	-	-	V
$_{CES}$	Collector-emitter leakage current	$_{CE}$=650V, $_{GE}$=0V	-	-	50	μA
$_{GES}$	Gate leakage current, forward	$_{GE}$=20V, $_{CE}$=0V	-	-	100	nA
	Gate leakage current, reverse	$_{GE}$=-20V, $_{CE}$=0V	-	-	-100	nA
$_{GE(th)}$	Gate-emi					

Symbol	Parameter

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$_F$	Diode forward voltage	$_F$=10				

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Typical performance characteristics

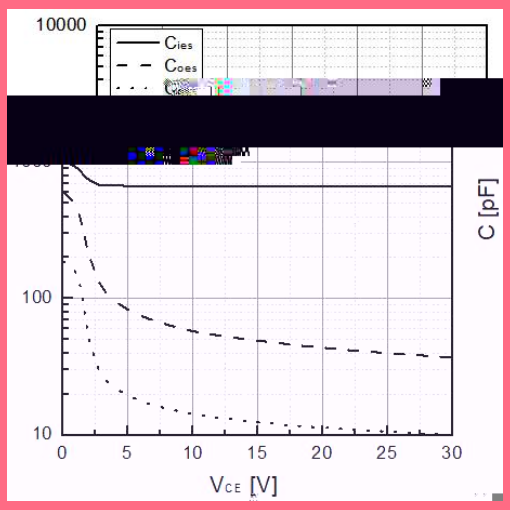


Fig 13. Typical capacitance as a function of $_{CE}$ (f=1Mhz, $_{GE}$=0V)

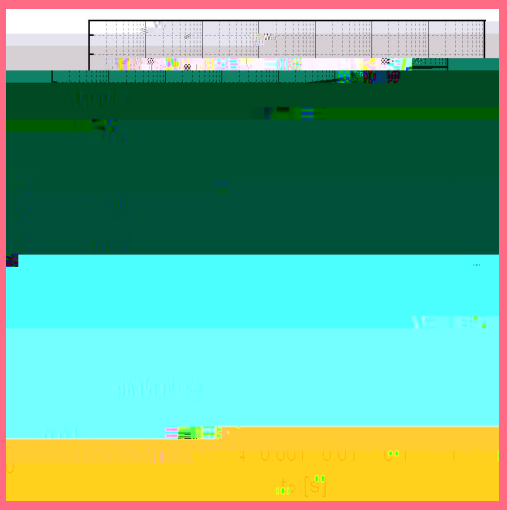


Fig 14. Transient thermal impedance, IGBT

Dimensions

Ref.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50	-	4.90	0.177	-	0.193
B	0.74	0.80	0.83	0		

Date	Revision	Changes
2024-03-20	Rev 1.1	Update
2025-02-06	Rev 1.2	Update
2025-04-08	Rev 1.3	Character U
2026-06-24	Rev 1.4	Update the

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